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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Nobuhiko HAYASHI et al.**

Serial No.: **09/898,043**

Group Art Unit: **2826**

Filed: **July 5, 2001**

Examiner: **Johannes P. Mondt**

P.T.O. Confirmation No.: **2566**

FOR: **NITRIDE-BASED SEMICONDUCTOR LIGHT EMITTING DEVICE AND NITRIDE BASED SEMICONDUCTOR LASER DEVICE** (as herein amended)

**AMENDMENT UNDER 37 C.F.R. §1.111**

Commissioner for Patents  
Washington, D.C. 20231

Date: **July 29, 2002**

Sir:

In response to the Office Action dated February 27, 2002, please amend the above-identified application as follows:

**IN THE TITLE OF THE INVENTION:**

Please amend the title to:

*Q!*  
NITRIDE-BASED SEMICONDUCTOR LIGHT EMITTING DEVICE AND NITRIDE  
BASED SEMICONDUCTOR LASER DEVICE

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Adjustment date: 07/16/2003 ELKHORN/AY1  
08/12/2002 AJENKINS 00000001 012340 09890043  
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